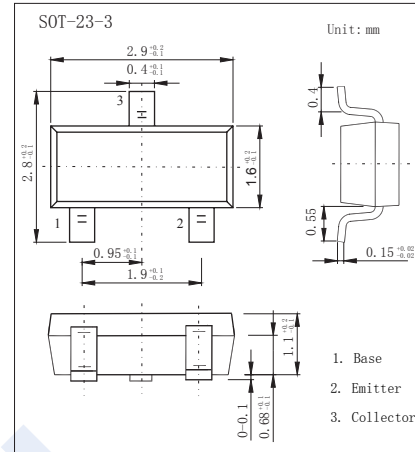


PNP Transistors

2SB1295-HF

■ Features

- Large current capacity.
- Low collector to emitter saturation voltage.
- Complimentary to 2SD1935-HF
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-15	V
Collector - Emitter Voltage	V _{CEO}	-15	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _C	-0.8	A
Collector Current - Pulse	I _{CP}	-3	A
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -100 μA, I _E =0	-15			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, R _{BE} =∞	-15			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _C =0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -12V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _C =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-5 mA, I _B =-0.5mA		-10	-25	mV
		I _C =-400 mA, I _B =-20mA		-100	-200	
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-400 mA, I _B =-20mA		-0.9	-1.2	V
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -50mA	135		600	
		V _{CE} = -2V, I _C = -800mA	80			
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f=1MHz		15		pF
Transition frequency	f _T	V _{CE} = -2V, I _E = 50mA		300		MHz

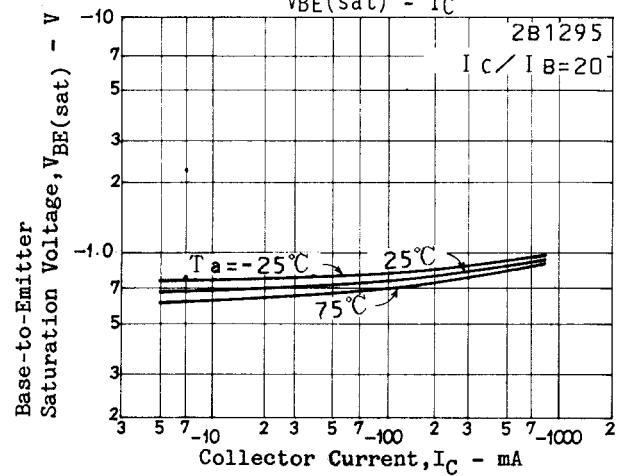
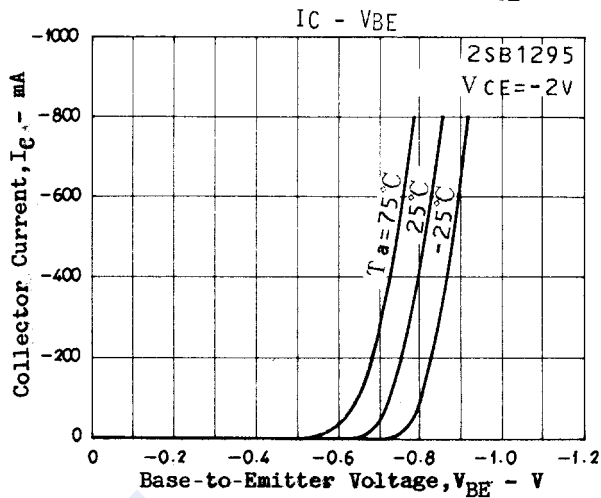
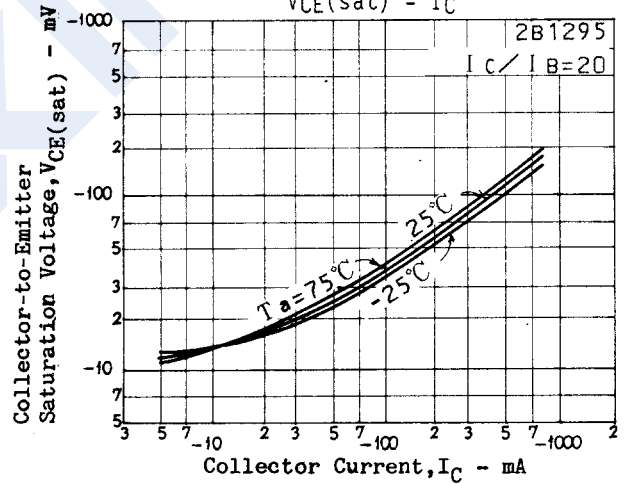
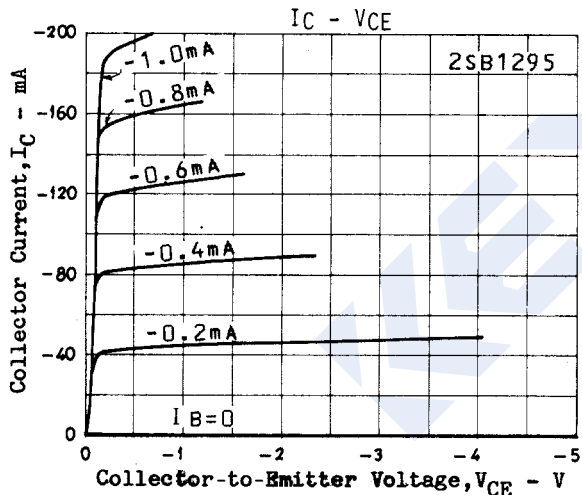
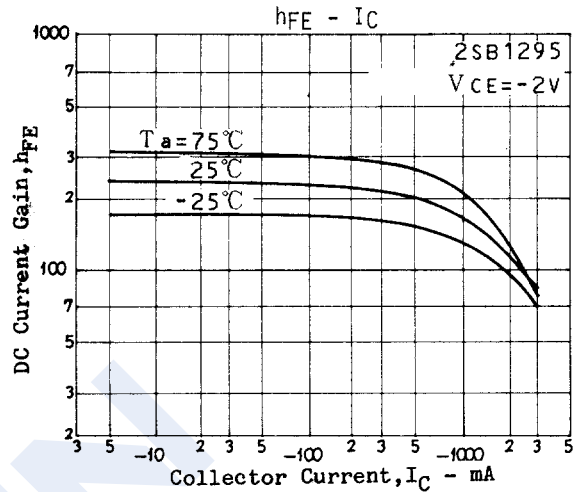
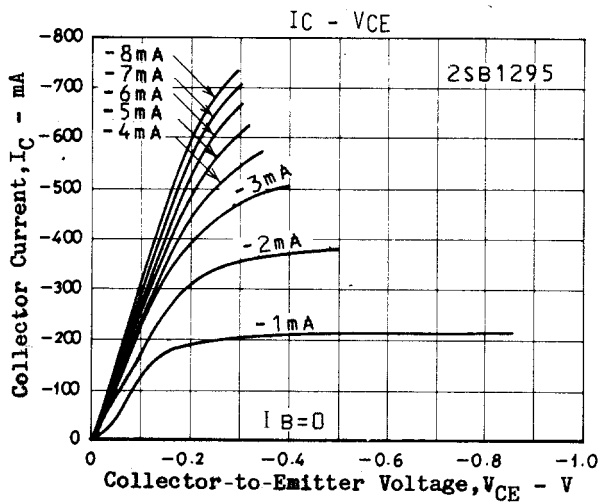
■ Classification of h_{FE}(1)

Type	2SB1295-UL5-HF	2SB1295-UL6-HF	2SB1295-UL7-HF
Range	135-270	200-400	300-600
Marking	UL5 _F	UL6 _F	UL7 _F

PNP Transistors

2SB1295-HF

■ Typical Characteristics



PNP Transistors

2SB1295-HF

■ Typical Characteristics

